



## DYNAMIC CHARACTERISTICS

APT40GP60B2DQ2(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		4610		pF	
$C_{oes}$	Output Capacitance			395			
$C_{res}$	Reverse Transfer Capacitance			25			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	Gate Charge		7.5		V	
$Q_g$	Total Gate Charge <sup>(3)</sup>	$V_{GE} = 15V$		135		nC	
$Q_{ge}$	Gate-Emitter Charge	$V_{CE} = 300V$		30			
$Q_{gc}$	Gate-Collector ("Miller") Charge	$I_C = 40A$		40			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 600V$	160			A	
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b> $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		20		ns	
$t_r$	Current Rise Time			29			
$t_{d(off)}$	Turn-off Delay Time			64			
$t_f$	Current Fall Time			45			
$E_{on1}$	Turn-on Switching Energy <sup>(4)</sup>			385			μJ
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>(5)</sup>		645				
$E_{off}$	Turn-off Switching Energy <sup>(6)</sup>		350	450			
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (125°C)</b> $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		20		ns	
$t_r$	Current Rise Time			29			
$t_{d(off)}$	Turn-off Delay Time			90			
$t_f$	Current Fall Time			70			
$E_{on1}$	Turn-on Switching Energy <sup>(4)</sup>			385			μJ
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>(5)</sup>			970			
$E_{off}$	Turn-off Switching Energy <sup>(6)</sup>			615	950		

## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.23	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			.67	
$W_T$	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④  $E_{on1}$  is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)  
Repetitive Rating: Pulse width limited by maximum junction temperature.

⑦ Continuous current limited by package lead temperature/

**APT Reserves the right to change, without notice, the specifications and information contained herein.**

# TYPICAL PERFORMANCE CURVES

# APT40GP60B2DQ2(G)

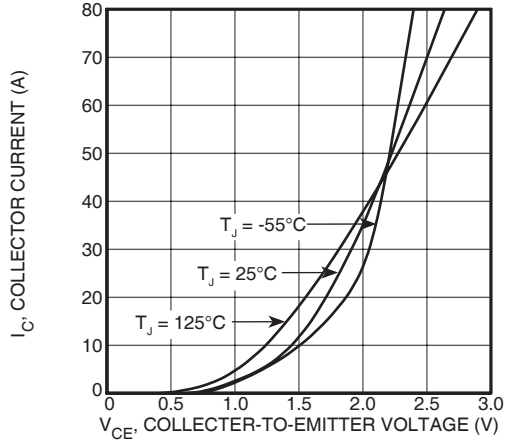


FIGURE 1, Output Characteristics( $T_J = 25^\circ\text{C}$ )

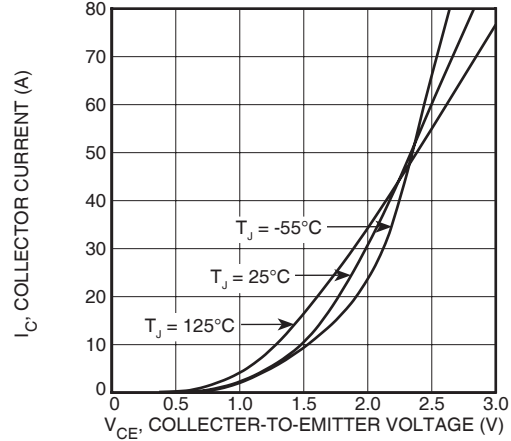


FIGURE 2, Output Characteristics ( $T_J = 125^\circ\text{C}$ )

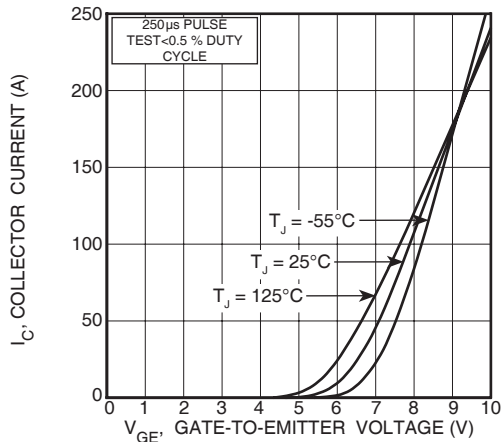


FIGURE 3, Transfer Characteristics

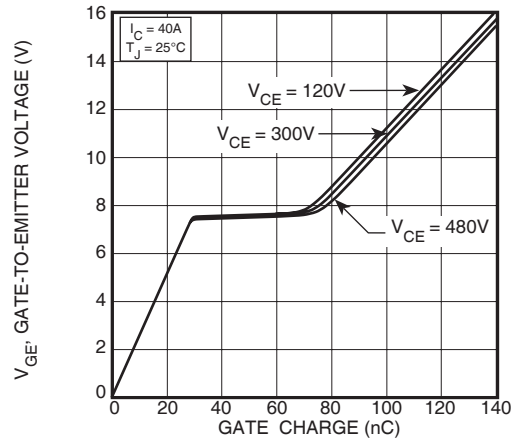


FIGURE 4, Gate Charge

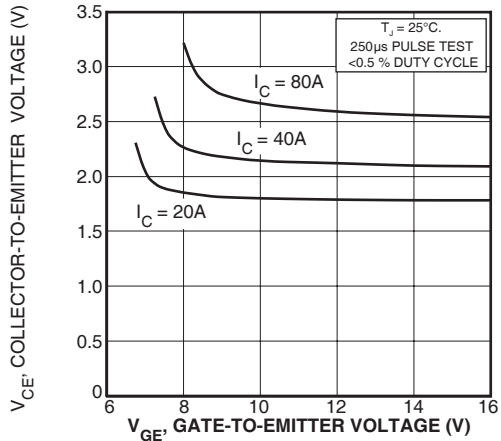


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

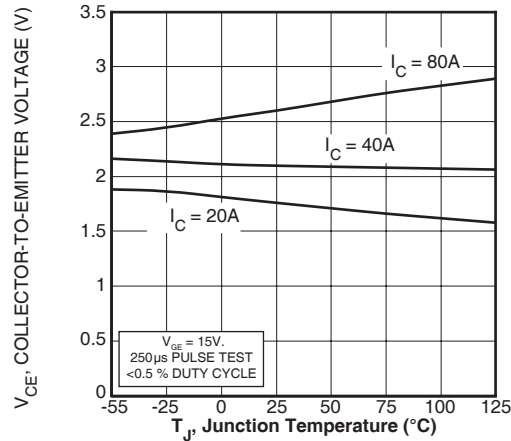


FIGURE 6, On State Voltage vs Junction Temperature

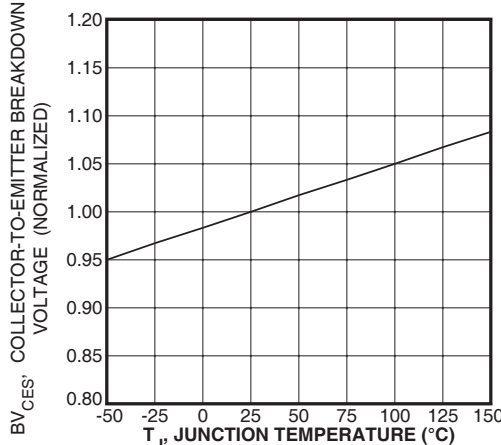


FIGURE 7, Breakdown Voltage vs. Junction Temperature

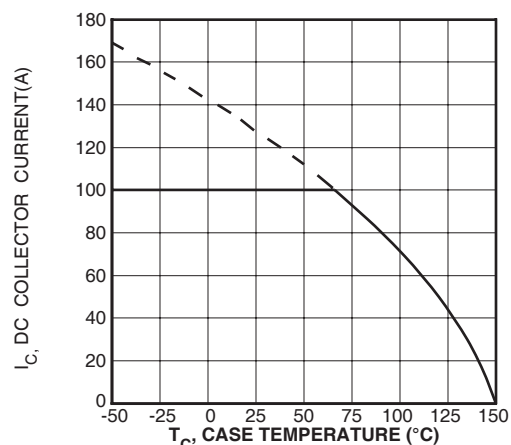


FIGURE 8, DC Collector Current vs Case Temperature

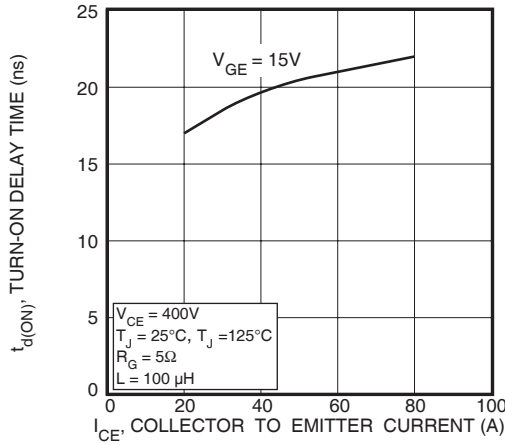


FIGURE 9, Turn-On Delay Time vs Collector Current

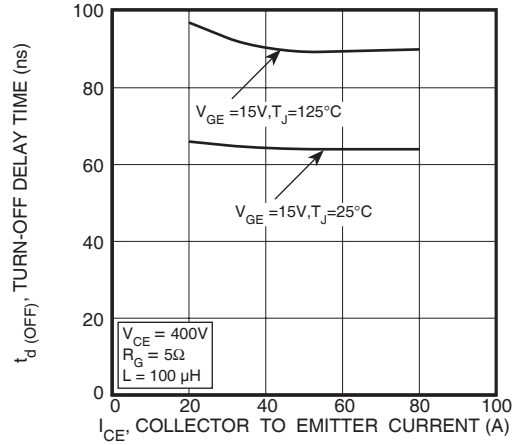


FIGURE 10, Turn-Off Delay Time vs Collector Current

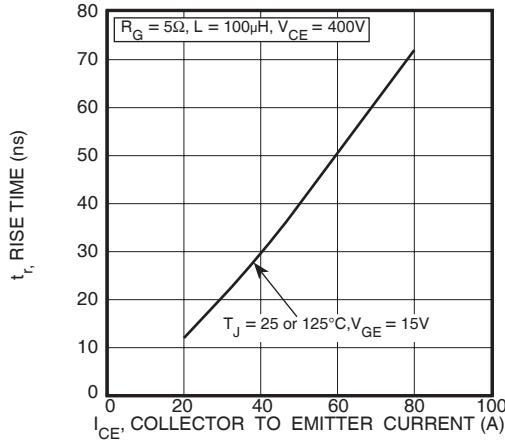


FIGURE 11, Current Rise Time vs Collector Current

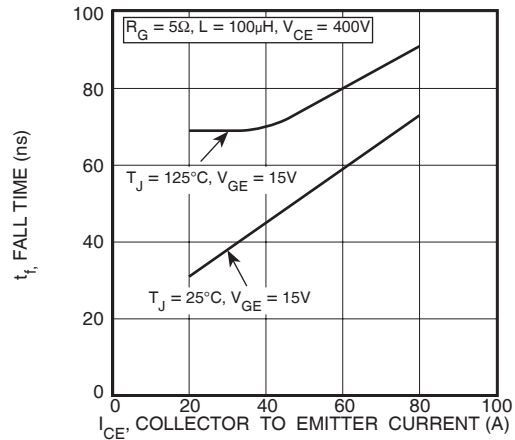


FIGURE 12, Current Fall Time vs Collector Current

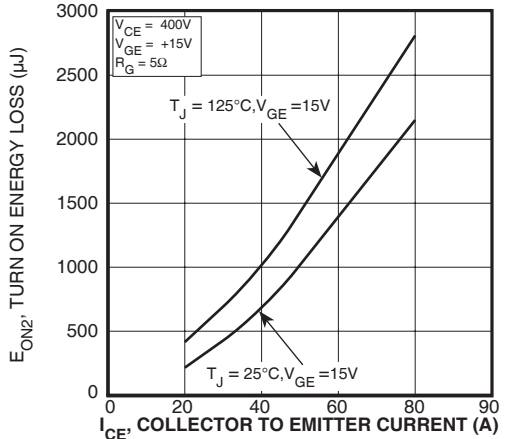


FIGURE 13, Turn-On Energy Loss vs Collector Current

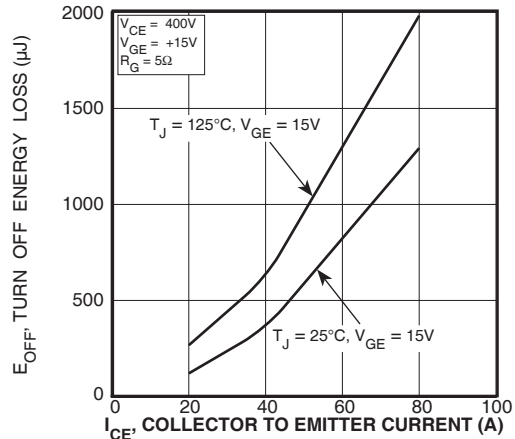


FIGURE 14, Turn Off Energy Loss vs Collector Current

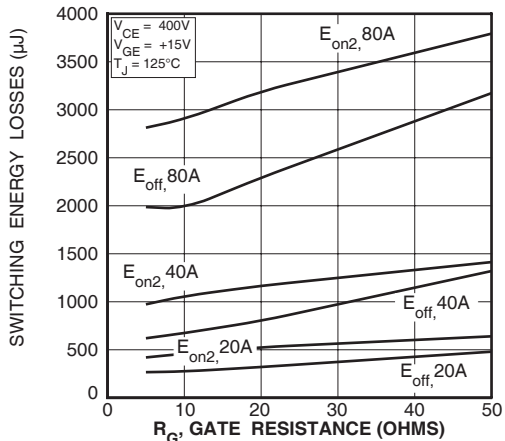


FIGURE 15, Switching Energy Losses vs. Gate Resistance

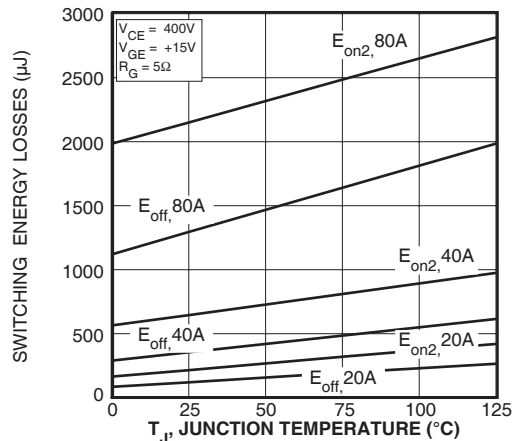


FIGURE 16, Switching Energy Losses vs Junction Temperature

**TYPICAL PERFORMANCE CURVES**

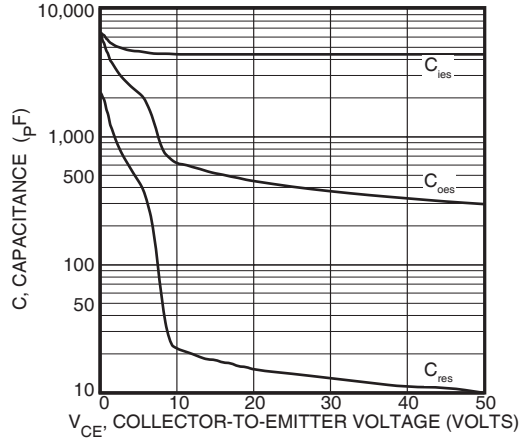


Figure 17, Capacitance vs Collector-To-Emitter Voltage

**APT40GP60B2DQ2(G)**

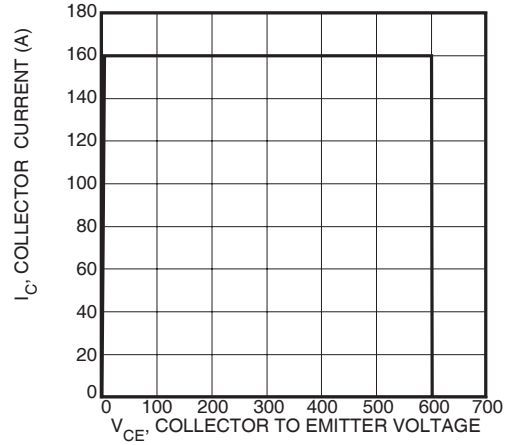


Figure 18, Minimum Switching Safe Operating Area

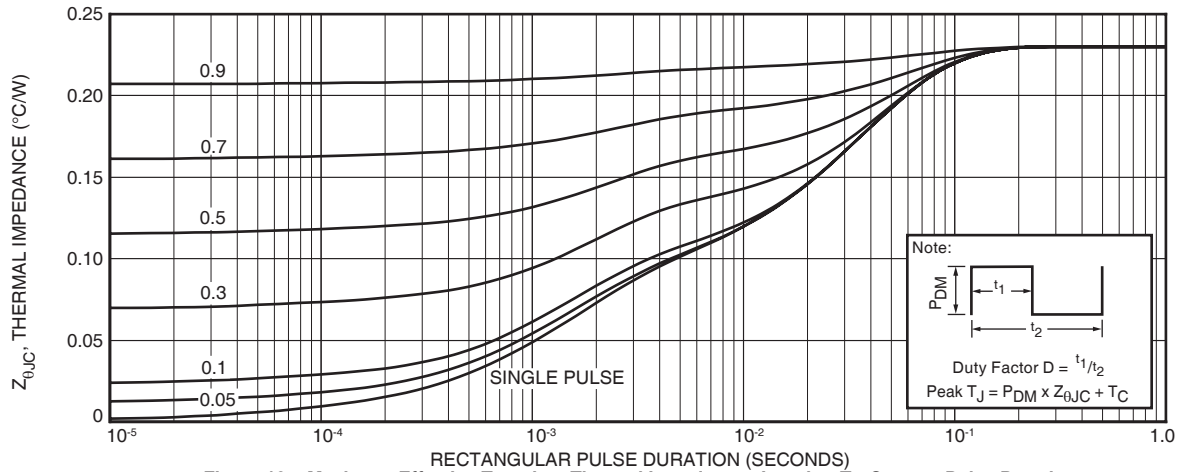


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

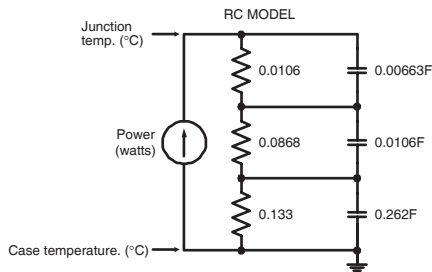


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

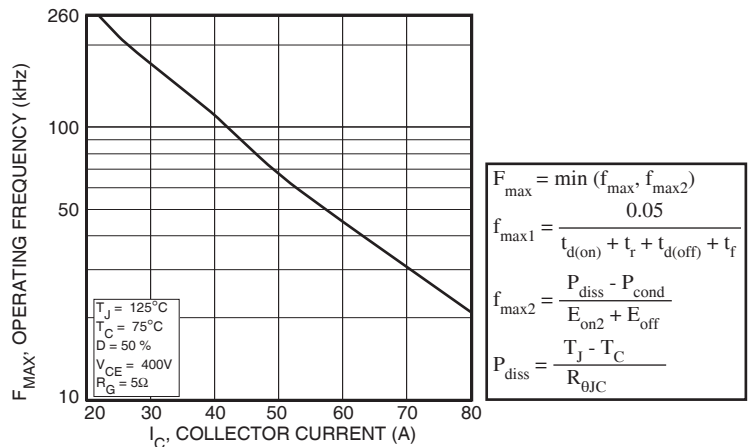


Figure 20, Operating Frequency vs Collector Current

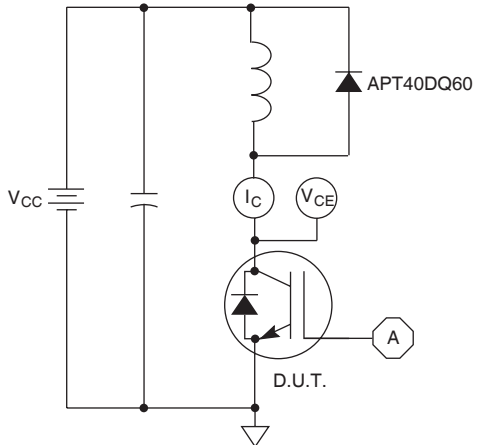


Figure 21, Inductive Switching Test Circuit

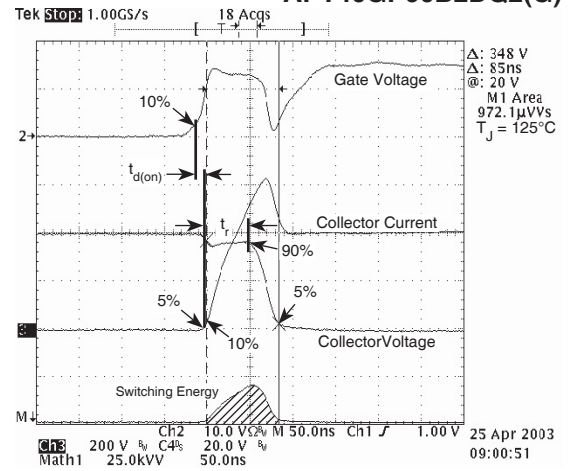


Figure 22, Turn-on Switching Waveforms and Definitions

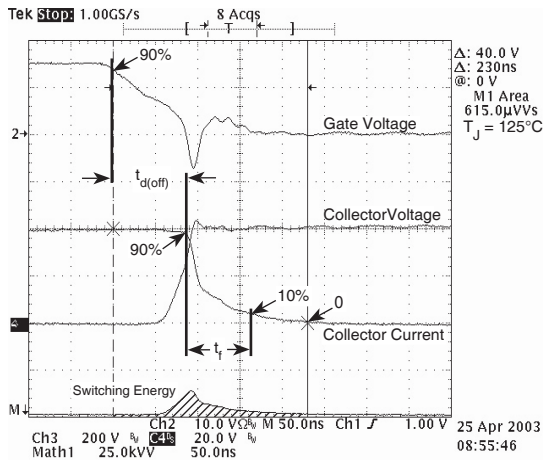


Figure 23, Turn-off Switching Waveforms and Definitions

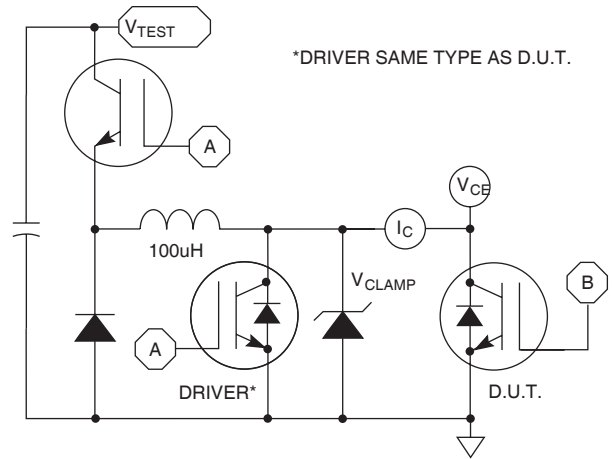


Figure 24,  $E_{ON1}$  Test Circuit

# ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

**MAXIMUM RATINGS**

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT40GP60B2DQ2(G)		UNIT
$I_F(AV)$	Maximum Average Forward Current ( $T_C = 111^\circ\text{C}$ , Duty Cycle = 0.5)		40	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)		63	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)		320	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$V_F$	Forward Voltage		$I_F = 40A$	2.0	Volts
			$I_F = 80A$	2.5	
			$I_F = 40A, T_J = 125^\circ\text{C}$	1.7	

**DYNAMIC CHARACTERISTICS**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ\text{C}$	-	22		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 40A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 25^\circ\text{C}$	-	25		
$Q_{rr}$	Reverse Recovery Charge		-	35		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	3	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 40A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 125^\circ\text{C}$	-	160		ns
$Q_{rr}$	Reverse Recovery Charge		-	480		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	6	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 40A, di_F/dt = -1000A/\mu s, V_R = 400V, T_C = 125^\circ\text{C}$	-	85		ns
$Q_{rr}$	Reverse Recovery Charge		-	920		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	20		Amps

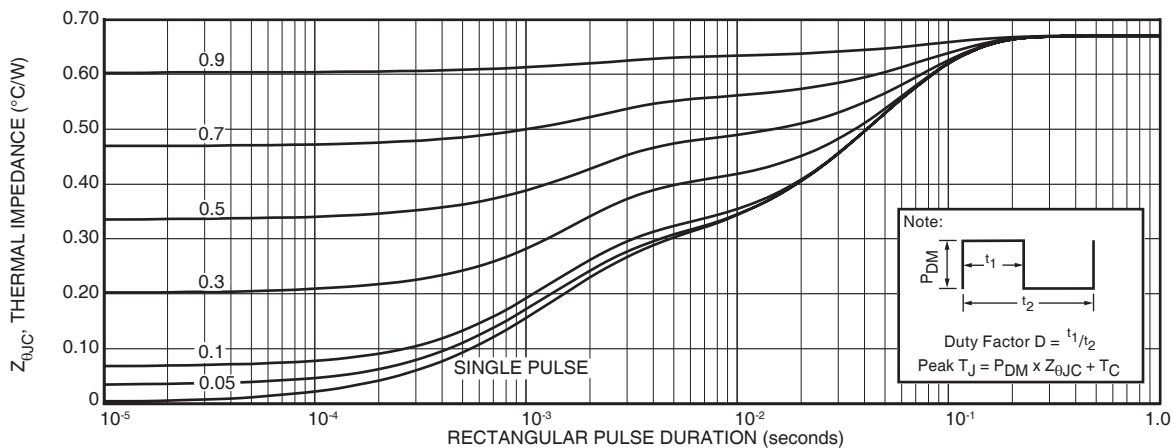


FIGURE 25a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

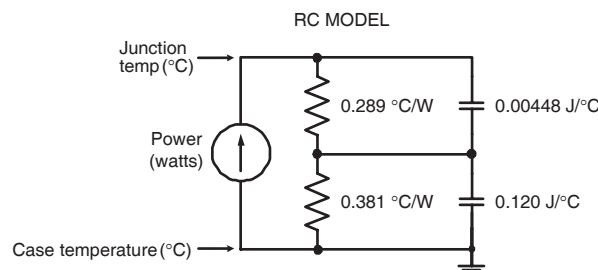


FIGURE 25b. TRANSIENT THERMAL IMPEDANCE

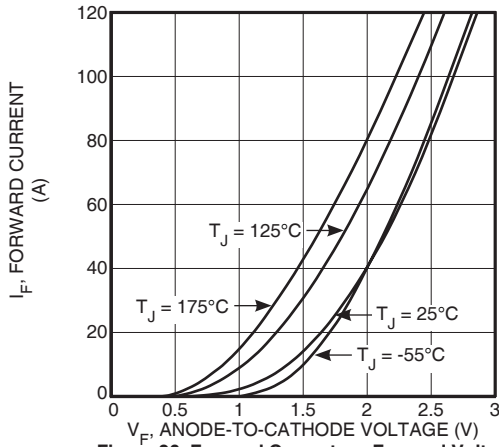


Figure 26. Forward Current vs. Forward Voltage

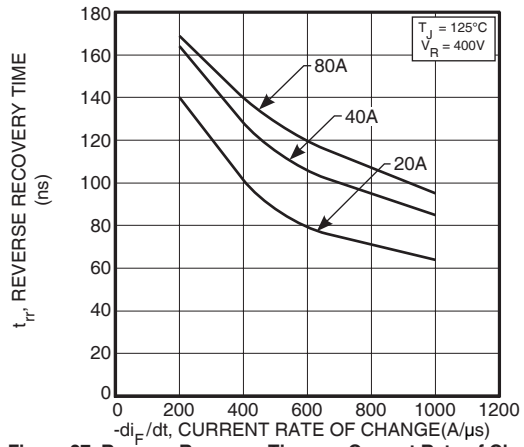


Figure 27. Reverse Recovery Time vs. Current Rate of Change

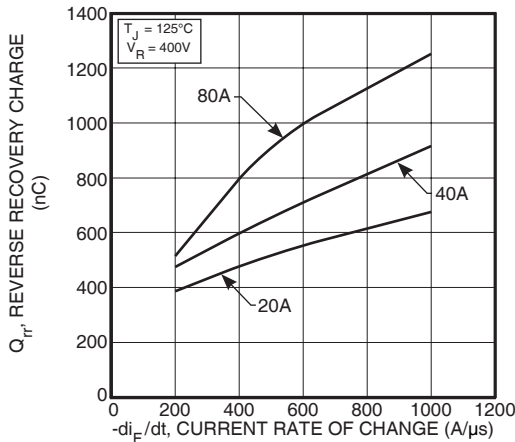


Figure 28. Reverse Recovery Charge vs. Current Rate of Change



Figure 29. Reverse Recovery Current vs. Current Rate of Change

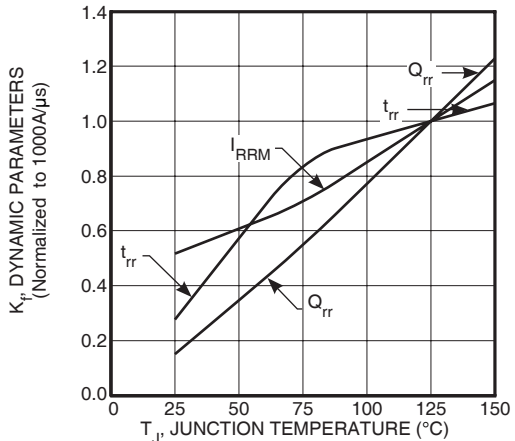


Figure 30. Dynamic Parameters vs. Junction Temperature

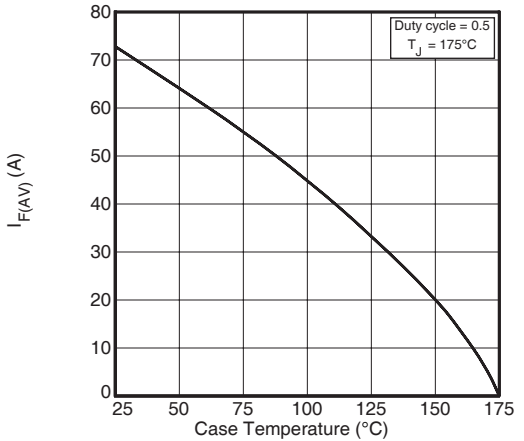


Figure 31. Maximum Average Forward Current vs. Case Temperature

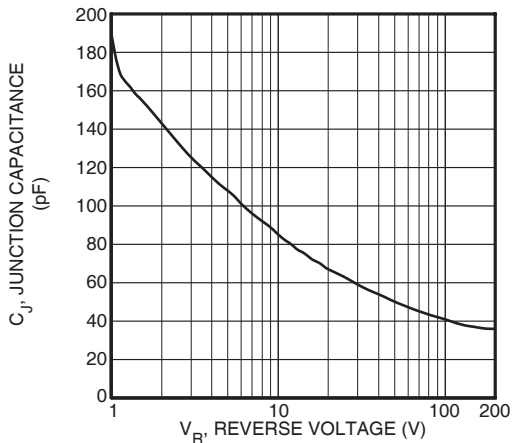


Figure 32. Junction Capacitance vs. Reverse Voltage



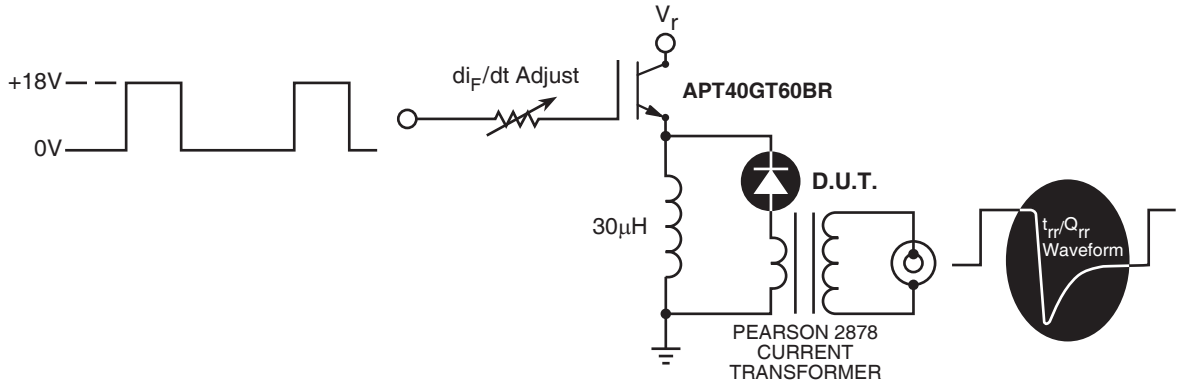


Figure 33. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

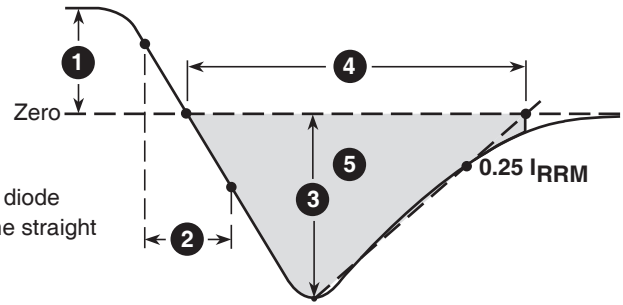
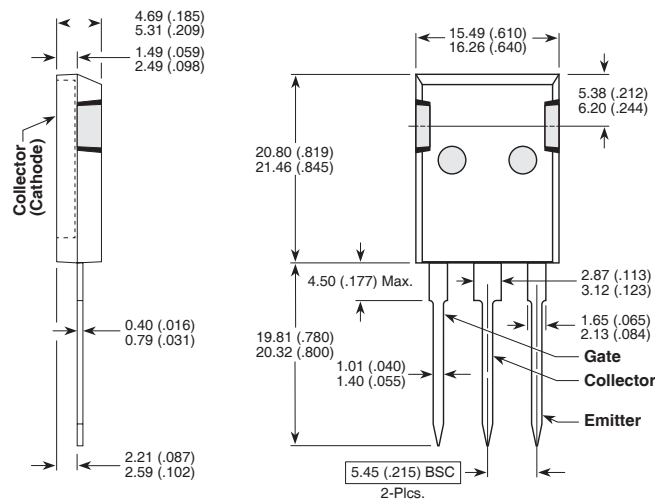


Figure 34, Diode Reverse Recovery Waveform and Definitions

### T-MAX™ (B2) Package Outline

Ⓜ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.